



JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

TO-252-2LK Plastic-Encapsulate Thyristors

CT406D 4Q TRIACs

MAIN CHARACTERISTICS

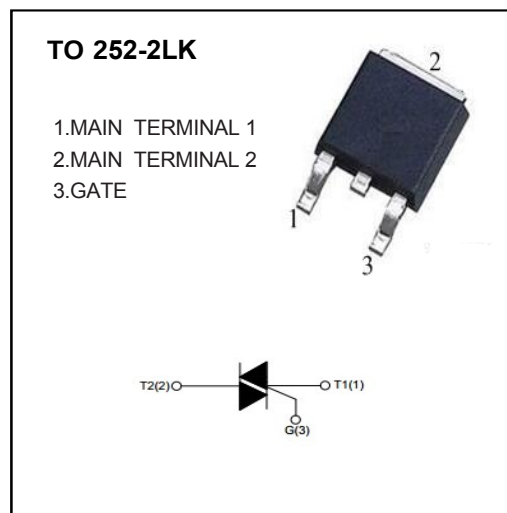
$I_{T(RMS)}$		6A
V_{DRM}/V_{RRM}	CT406D-600S/C	600V
	CT406D-800S/C	800V
V_{TM}		1.55V

FEATURES

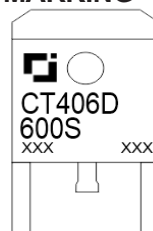
- NPNPN 5-layer Structure TRIACs
- Mesa Glass Passivated Technology
- Multi Layers Metal Electrodes
- High Junction Temperature
- Good Commutation Performance

APPLICATIONS

- Heater Control
- Motor Speed Controller
- Mixer



MARKING



CT406D:Series Code
600S:Depends on V_{DRM}
and I_{GT}
XXX:Internal Code

ABSOLUTE RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Test condition		Value	Unit
V_{DRM}/V_{RRM}	Repetitive peak off-state voltage	$T_j=25^{\circ}\text{C}$	CT406D-600S/C	600	V
			CT406D-800S/C	800	V
$I_{T(RMS)}$	RMS on-state current	TO-252-2LK($T_C \leq 110^{\circ}\text{C}$), Fig. 1,2		6	A
I_{TSM}	Non repetitive surge peak on-state current	Full sine wave, $T_j(\text{init})=25^{\circ}\text{C}$, $t_p=20\text{ms}$; Fig. 3,5		60	A
I^2t	I^2t value	$t_p=10\text{ms}$		18	A^2s
di_T/dt	Critical rate of rise of on-state current	$I_G=2 \cdot I_{GT}$, $t_r \leq 10\text{ns}$, $F=120\text{Hz}$, $T_j=125^{\circ}\text{C}$	I - II -III	50	$\text{A}/\mu\text{s}$
			IV	10	
I_{GM}	Peak gate current	$t_p=20\mu\text{s}$, $T_j=125^{\circ}\text{C}$		2	A
$P_{G(AV)}$	Average gate power	$T_j=125^{\circ}\text{C}$		0.5	W
T_{STG}	Storage temperature			-40~+150	$^{\circ}\text{C}$
T_j	Operating junction temperature			-40~+125	

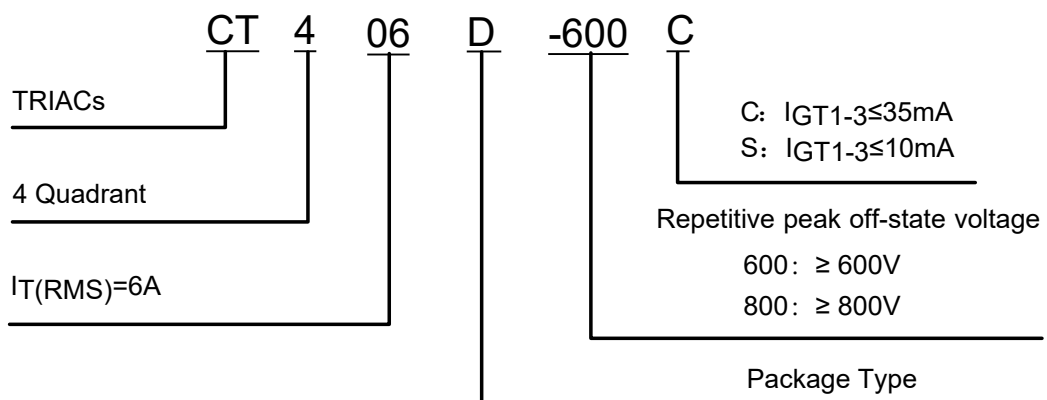
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test condition		Value		Unit
				S	C	
I _{GT}	Gate trigger current	V _D =12V, I _T =0.1A, T _J =25°C, Fig. 6	I - II -III	≤8	≤20	mA
			IV	≤10	≤35	
V _{GT}	Gate trigger voltage	T _J =25°C, Fig. 6	I - II -III	≤1.3		V
V _{GD}	Non-triggering gate voltage	V _D =V _{DRM} , T _J =125°C		≥0.2		V
I _H	Holding current	V _D =12V, I _{GT} =0.1A, T _J =25°C, Fig. 6	I - II -III - IV	≤10	≤15	mA
I _L	Latching current		I -III - IV	≤15	≤20	mA
			II	≤20	≤25	mA
dV _D /dt	Critical rate of rise of off-state	V _D =67%V _{DRM} , Gate Open T _J =125°C		≥10	≥20	V/μs
V _{TM}	On-state Voltage	I _{TM} =8.5A, tp=380 μ s , Fig. 4		≤1.55		V
I _{DRM} / I _{RRM}	Repetitive peak off-state current	V _D =V _{DRM} /V _{RRM} , T _J =25°C		≤5	≤5	μA
		V _D =V _{DRM} /V _{RRM} , T _J =125°C		≤1	≤1	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th} (j-c)	Junction to case (AC)	TO-252-2LK	2.1	°C/W
R _{th} (j-a)	Junction to ambient	TO-252-2LK	70	°C/W

PART NUMBER



CHARACTERISTICS CURVES

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

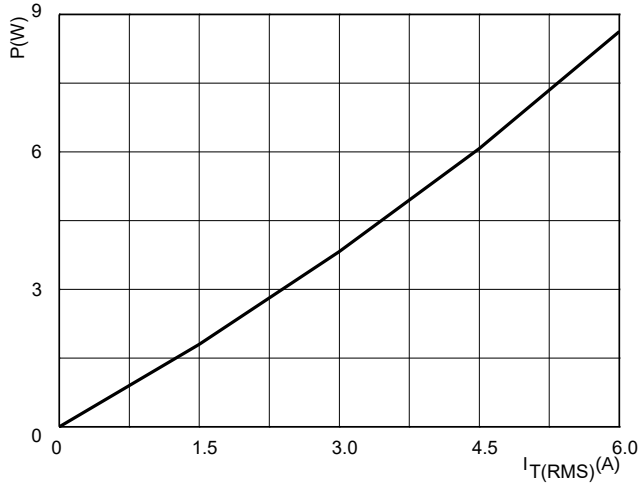


FIG.2: RMS on-state current versus case temperature (full cycle)

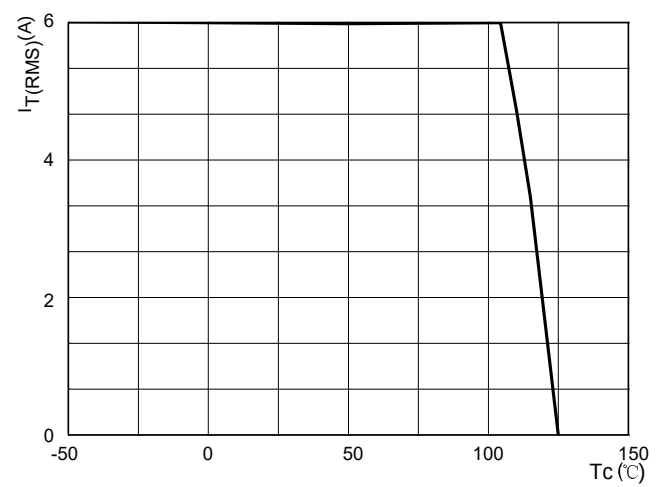


FIG.3: Surge peak on-state current versus number of cycles

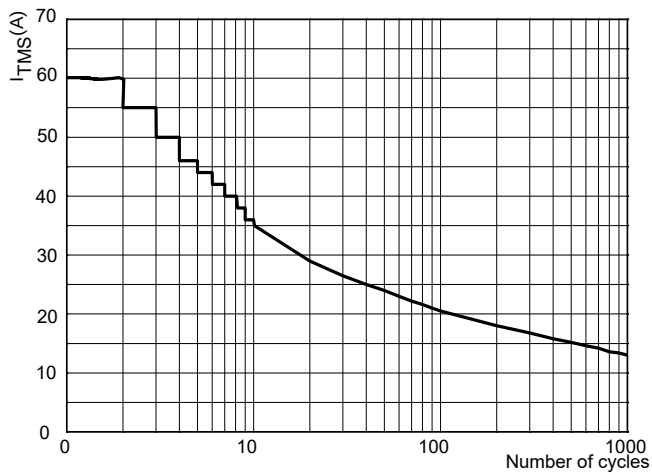


FIG.4: On-state characteristics (maximum values)

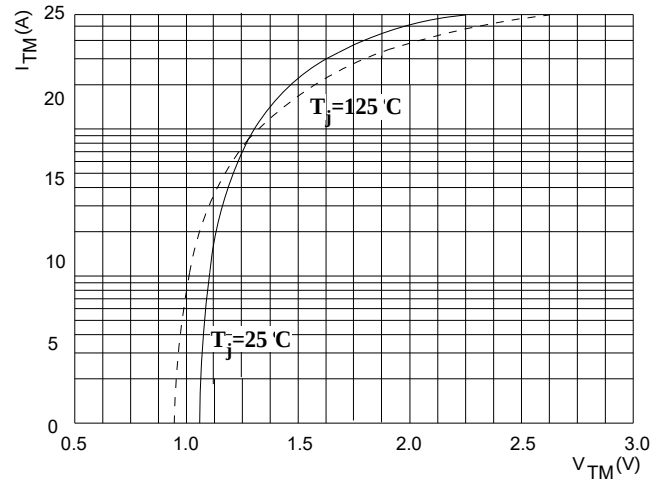


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$

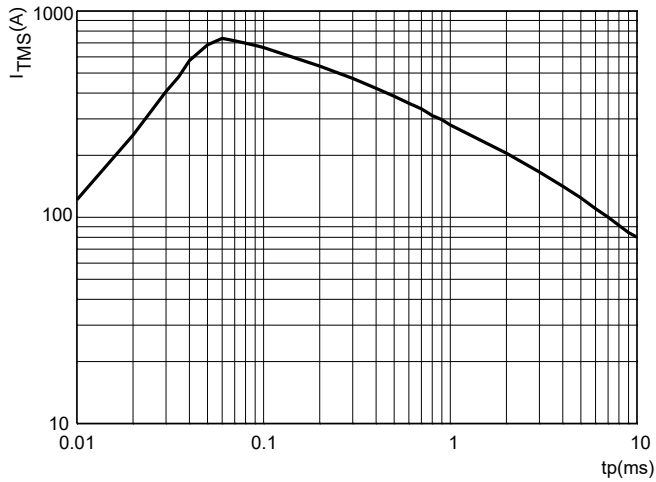
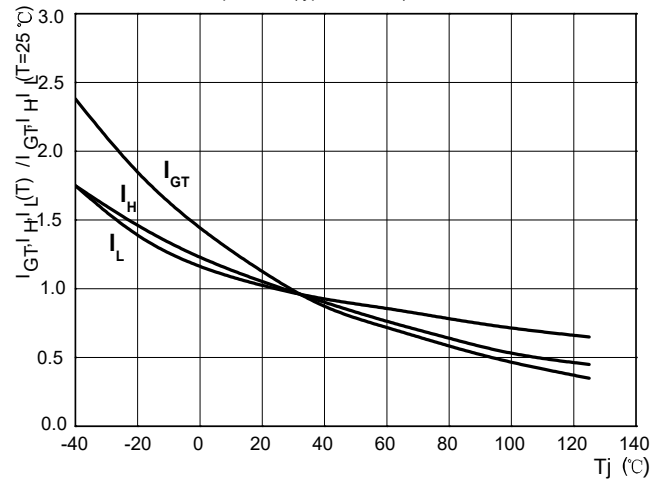
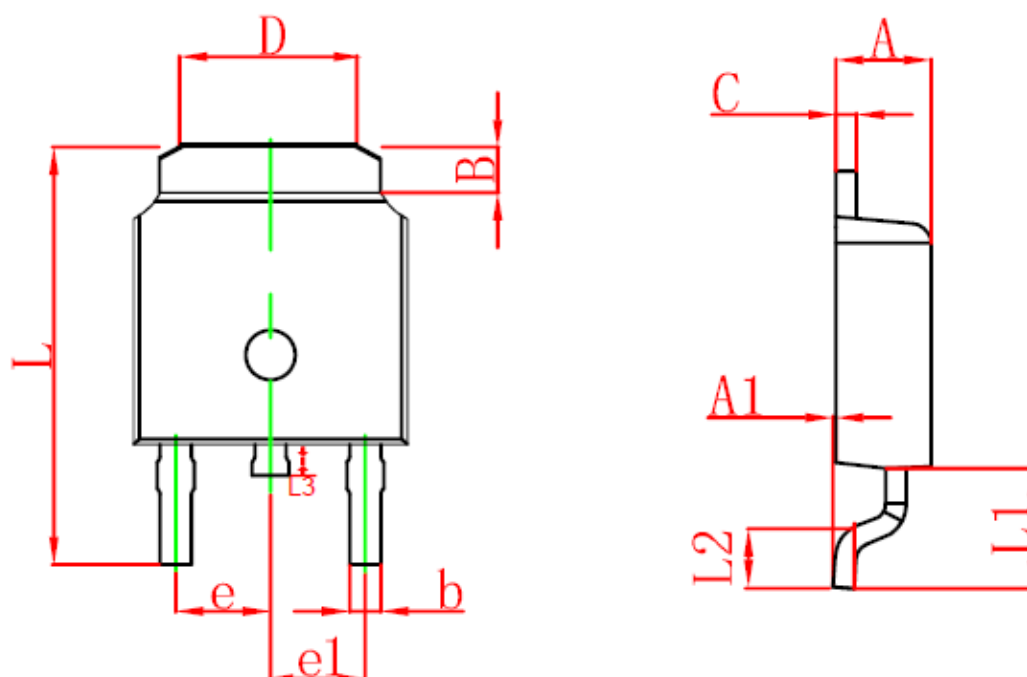


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



TO-252-2LK PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	2.100	2.500
A1	0.000	0.127
B	1.070	1.470
b	0.710	0.810
C	0.700	0.900
D	3.400	3.800
e	2.250	2.350
e1	2.250	2.350
L	10.000	10.400
L1	2.600	3.000
L2	1.400	1.700
L3	0.600	1.000